each of said introduction holes is designed to pass the radicals only to the film deposition chamber.

wherein a cleaning gas is introduced through said cleaning gas feeder to produce plasma in the plasma generator and generate radicals, and the radicals are introduced through said introduction holes to said film deposition chamber to strike the substrate and thereby clean the substrate.

3. (Amended) A substrate cleaning method comprising:

depositing a silicon-based film on a substrate,

converting the silicon-based film to a crystalline silicon film by laser annealing,

depositing a gate insulating film on said crystalline film by a CVD system comprised of a separate film deposition chamber and plasma generation chamber using a lower plate with introduction holes, wherein said lower plate is connected to ground and each of the introduction holes is designed to pass radical only in plasma.

generating plasma by use of a cleaning gas in said CVD system at a stage before forming the gate insulating film and emitting only the radicals in the plasma through the introduction holes of the lower plate on the crystalline silicon film to clean its surface.

REMARKS

Claims 1-4 are pending herein. By this Amendment, claims 1 and 3 are amended. No claim is cancelled and no new claim is added. Support for the Amendment of claims 1 and 3 can be found in the specification, for example, at page 8, lines 17-18. Thus, this Amendment does not introduce new matter.

The attached Appendix includes marked-up copies of each rewritten claim (37 C.F.R. §1.121(c)(1)(ii)).